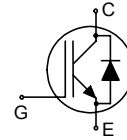


LightMOS Power Transistor

- New revolutionary high voltage technology designed for ZVS-switching in lamp ballasts
- IGBT with integrated reverse diode
- Avalanche rated
- 150°C operating temperature



Type	V_{CE}	I_C	$V_{CE(sat), T_j=25^\circ C}$	$T_{j,max}$	Package	Ordering Code
ILP03N60	600V	3.0A	2.9A	150°C	P-TO-220-3-1	Q67040-S4628
ILB03N60	600V	3.0A	2.9V	150°C	P-TO-263-3-2	Q67040-S4627
ILD03N60	600V	3.0A	2.9V	150°C	P-TO-252-3-1	Q67040-S4625

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current	I_C		A
$T_C = 25^\circ C$		4.5	
$T_C = 100^\circ C$		3	
Pulsed collector current, t_p limited by $T_{j,max}$, $t_p < 10$ ms	$I_{C,puls}$	9	
Pulsed collector current, t_p limited by $T_{j,max}$		5.5	
Diode forward current	I_F		
$T_C = 25^\circ C$		4	
$T_C = 100^\circ C$		2.5	
Diode pulsed current, t_p limited by $T_{j,max}$, $t_p < 10$ ms	$I_{F,puls}$	9	
Diode pulsed current, t_p limited by $T_{j,max}$		5.5	
Avalanche energy, single pulse $I_C=0.8A$, $V_{CE}=50V$	E_{AS}	0.32	mJ
Gate-emitter voltage	V_{GE}	± 30	V
Reverse diode dv/dt	dv/dt	1 ¹	V/ns
$I_C \leq 3A$, $V_{CE} \leq 450V$, $T_{j,max} \leq 150^\circ C$			
Power dissipation	P_{tot}	27	W
$T_C = 25^\circ C$			
Operating junction and storage temperature	T_{stg}	-55...+150	°C
Soldering temperature for 10 s (according to JEDEC J-STA-020A)	T_s	255	

¹ Reverse diode of transistor is commutated with same device according to figure C. With application relevant values $I_C \leq 1.5A$ and $R_G \geq 50\Omega$, dv/dt of the reverse diode is within its specification.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		4.7	K/W
Diode thermal resistance, junction – case	R_{thJCD}		10	
Thermal resistance, junction – ambient	R_{thJA}		62	
SMD version, device on PCB: @ min. footprint @ 6cm ² cooling area ¹	R_{thJA}		75 50	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0\text{V}, I_C=0.5\text{mA}$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=10\text{V}, I_C=3.0\text{A}$ $T_j=25^\circ\text{C}$	-	2.3	2.9	
		$T_j=150^\circ\text{C}$	-	2.7		
Diode forward voltage	V_F	$V_{GE}=10\text{V}, I_C=0.8\text{A}$ $T_j=25^\circ\text{C}$	-	1.5	-	
		$T_j=150^\circ\text{C}$	-	1.5	-	
Diode forward voltage	V_F	$V_{GE}=0\text{V}, I_F=3.0\text{A}$ $T_j=25^\circ\text{C}$	-	1.5	1.8	
		$T_j=150^\circ\text{C}$	-	1.6		
Diode forward voltage	V_F	$V_{GE}=0\text{V}, I_F=0.8\text{A}$ $T_j=25^\circ\text{C}$	-	1.0	-	
		$T_j=150^\circ\text{C}$	-	1.0	-	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=30\mu\text{A}, V_{CE}=V_{GE}$	2.1	3.0	3.9	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600\text{V}, V_{GE}=0\text{V}$ $T_j=25^\circ\text{C}$	-	1	20	μA
		$T_j=150^\circ\text{C}$	-	-	250	

¹ Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for drain connection. PCB is vertical without blown air.



ILP03N60, ILB03N60 ILD03N60

Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=3.0A$	-	1.5	-	S

Capacities, Gate Charge, at $T_j=25\text{ }^\circ\text{C}$

Input capacitance	C_{iss}	$V_{CE}=25\text{V}$,	-	110	-	pF
Output capacitance	C_{oss}	$V_{GE}=0\text{V}$,	-	6	-	
Reverse transfer capacitance	C_{rss}	$f=1\text{MHz}$	-	4	-	
Gate to emitter charge	Q_{GE}	$V_{CE}=400\text{V}$,	-	1	-	nC
Gate to collector charge	Q_{GC}	$I_C=3.0\text{A}$,	-	5.5	-	
Gate total charge	Q_G	$V_{GE}=10\text{V}$	-	8.5	-	
Gate plateau voltage	V_m		-	6.5	-	V
Gate to emitter charge	Q_{GE}	$V_{CE}=400\text{V}$,	-	0.5	-	nC
Gate to collector charge	Q_{GC}	$I_C=0.8\text{A}$,	-	4.0	-	
Gate total charge	Q_G	$V_{GE}=10\text{V}$	-	8	-	
Gate plateau voltage	V_m		-	3.5	-	V

Switching Characteristic, Inductive Load, at $T_j=25\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$V_{CC}=400\text{V}$,	-	15	-	ns
Rise time	t_r	$I_C=0.8\text{A}$,	-	35	-	
Turn-off delay time	$t_{d(off)}$	$V_{GE}=0/10\text{V}$,	-	100	-	
Fall time	t_f	$R_G=60\Omega$,	-	100	-	
Turn-on energy	E_{on}^3	$C_\sigma=0\text{nF}$	-	12	-	μJ
Turn-off energy	E_{off}	(C_σ : relief capacitor)	-	20	-	
Turn-off energy	E_{off}	$C_\sigma=1\text{nF}$	-	8	-	

Switching Characteristic, Inductive Load, at $T_j=150\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$V_{CC}=400\text{V}$,	-	20	-	ns
Rise time	t_r	$I_C=0.8\text{A}$,	-	45	-	
Turn-off delay time	$t_{d(off)}$	$V_{GE}=0/10\text{V}$,	-	120	-	
Fall time	t_f	$R_G=60\Omega$,	-	120	-	
Turn-on energy	E_{on}^3	$C_\sigma=0\text{nF}$	-	15	-	μJ
Turn-off energy	E_{off}	(C_σ : relief capacitor)	-	28	-	
Turn-off energy	E_{off}	$C_\sigma=1\text{nF}$	-	12	-	

³ E_{on} includes SDP04S60 diode commutation losses

Switching Characteristic, Inductive Load, at $T_j=25\text{ }^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Reverse diode Characteristic (switching in half bridge configuration with same transistor according to figure C)						
Reverse recovery time	t_{rr}	$V_R=400\text{V},$ $I_F=0.8\text{A},$ $V_{GE}=0/10\text{V},$ $R_G=80\Omega$	-	90	-	ns
Reverse recovery charge	Q_{rr}		-	0.27	-	μC
Peak reverse recovery current	I_{rrm}		-	5.5	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	300	-	$\text{A}/\mu\text{s}$
Reverse recovery time	t_{rr}	$V_R=400\text{V},$ $I_F=3\text{A},$ $V_{GE}=0/10\text{V},$ $R_G=80\Omega$	-	250	-	ns
Reverse recovery charge	Q_{rr}		-	0.75	-	μC
Peak reverse recovery current	I_{rrm}		-	8	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	300	-	$\text{A}/\mu\text{s}$

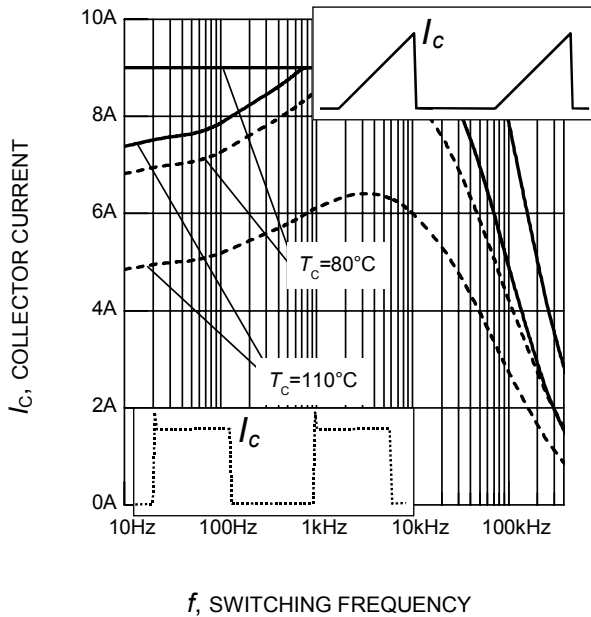


Figure 1. Collector current as a function of switching frequency
 ($T_j \leq 150^\circ\text{C}$, $D = 0.5$, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/+15\text{V}$, $R_G = 80\Omega$)

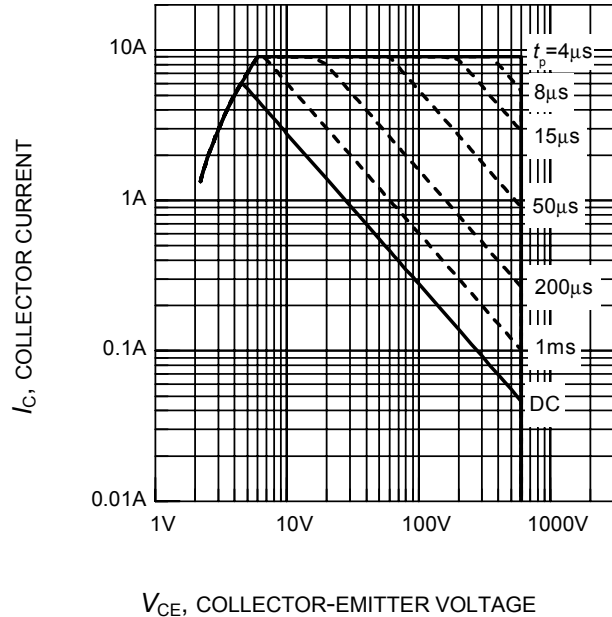


Figure 2. Safe operating area
 ($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)

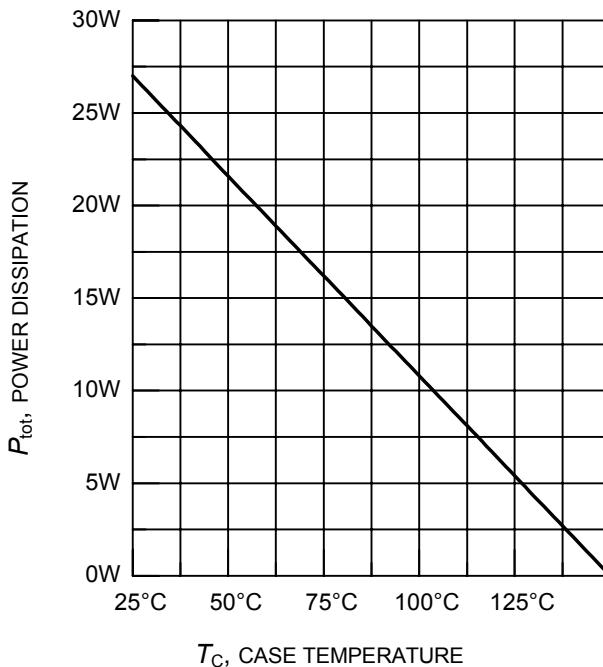


Figure 3. Power dissipation as a function of case temperature
 ($T_j \leq 150^\circ\text{C}$)

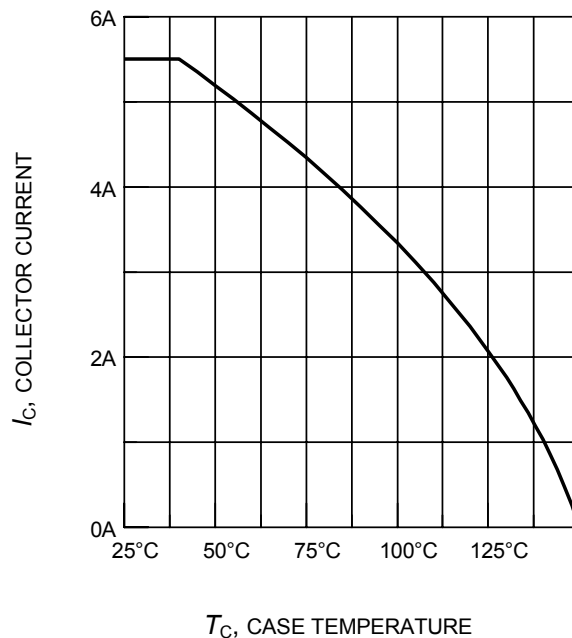


Figure 4. Collector current as a function of case temperature
 ($V_{GE} \leq 15\text{V}$, $T_j \leq 150^\circ\text{C}$)

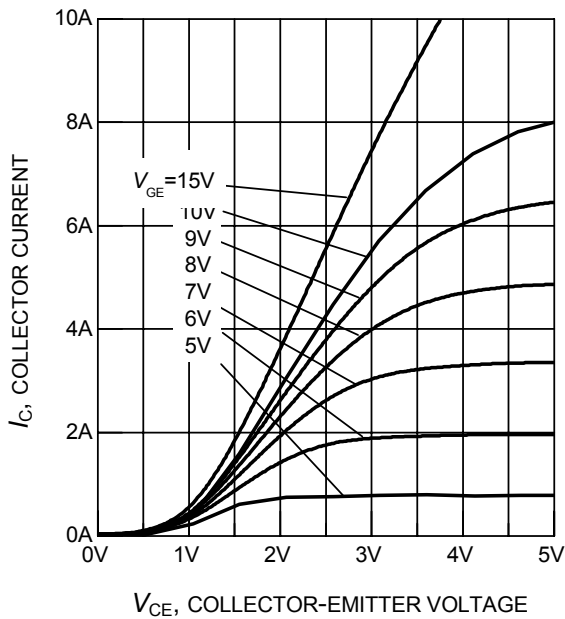


Figure 5. Typical output characteristics
($T_j = 25^\circ\text{C}$)

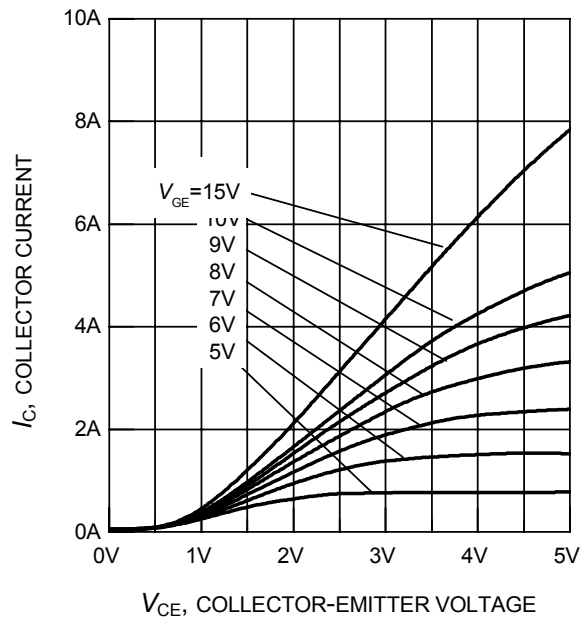


Figure 6. Typical output characteristics
($T_j = 150^\circ\text{C}$)

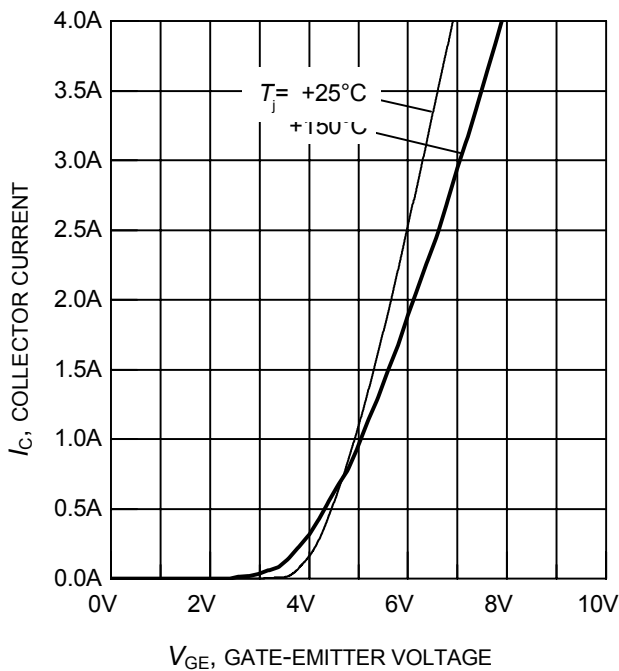


Figure 7. Typical transfer characteristics
($V_{CE} = 20\text{V}$)

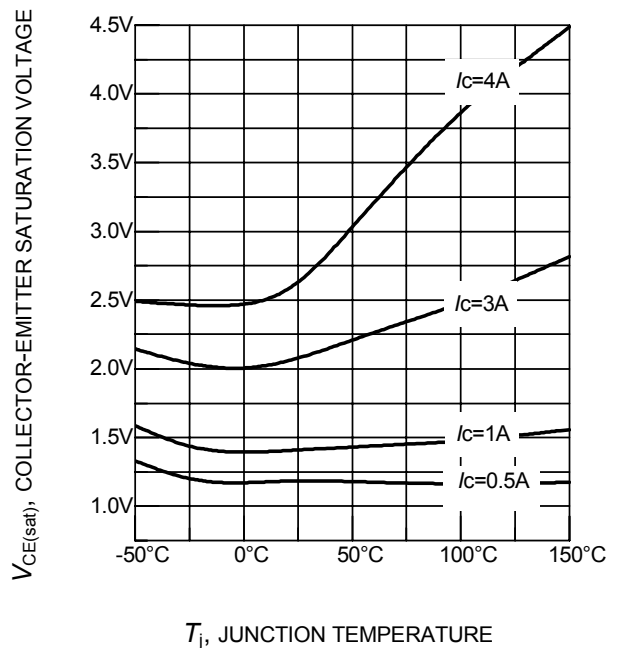


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 10\text{V}$)

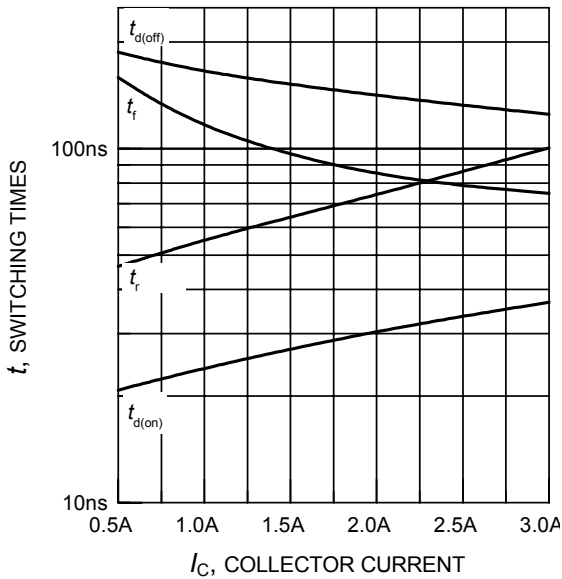


Figure 9. Typical switching times as a function of collector current
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $R_G = 80\Omega$, Dynamic test circuit in Figure E)

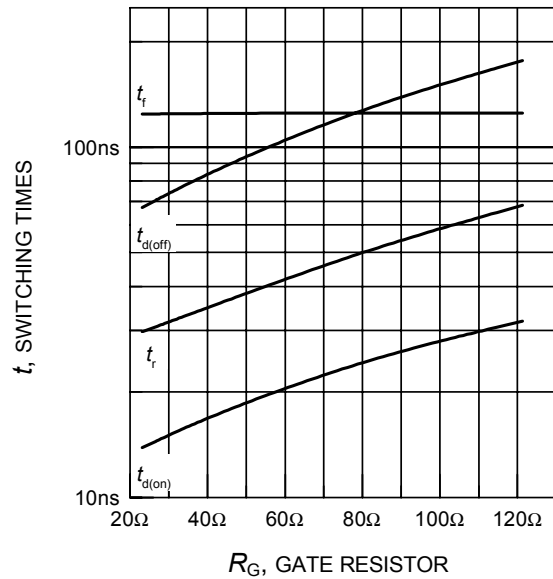


Figure 10. Typical switching times as a function of gate resistor
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $I_C = 1\text{A}$, Dynamic test circuit in Figure E)

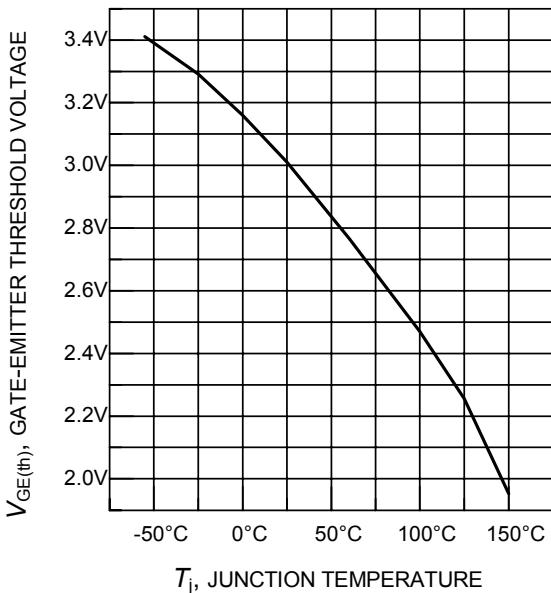


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
($I_C = 30\mu\text{A}$)

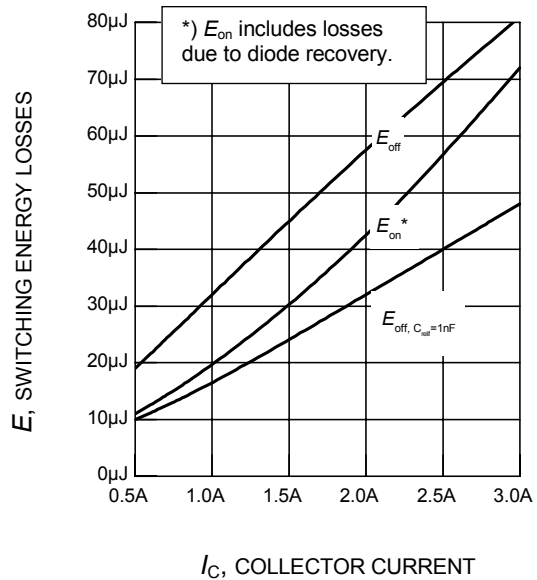


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $R_G = 80\Omega$, $C = 0/1\text{nF}$, Dynamic test circuit in Figure E)

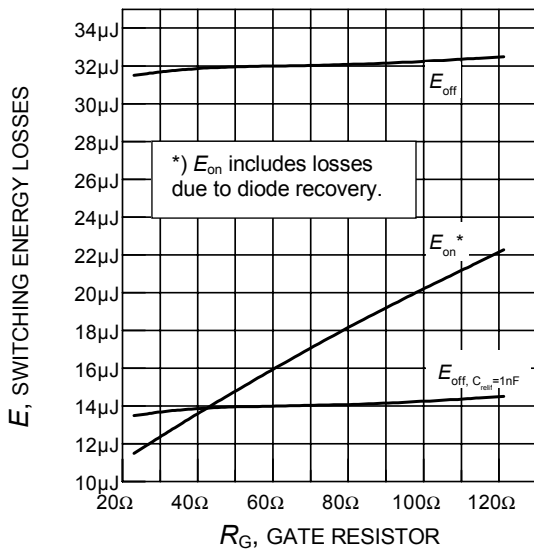


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $I_C = 1\text{A}$, Dynamic test circuit in Figure E)

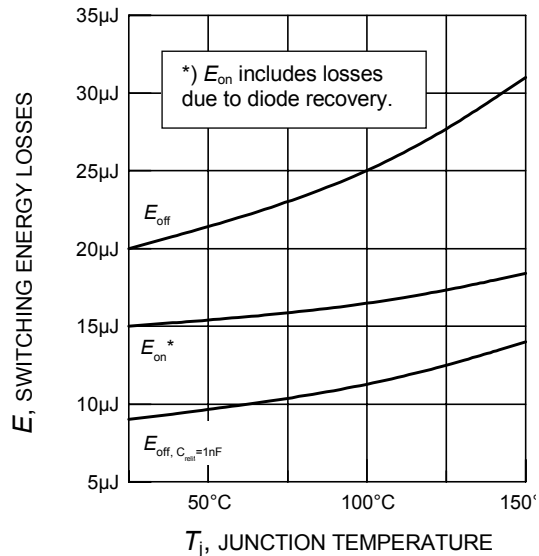


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+10\text{V}$, $I_C = 1\text{A}$, $R_G = 80\Omega$, Dynamic test circuit in Figure E)

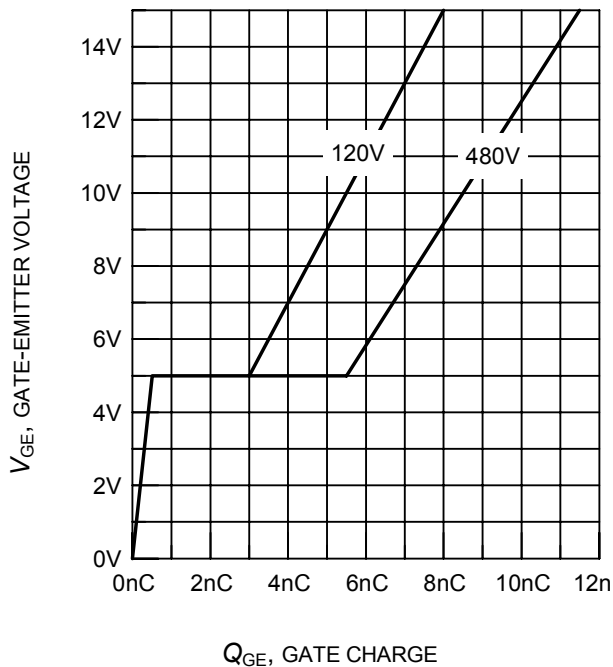


Figure 16. Typical gate charge
($I_C = 0.8\text{A}$)

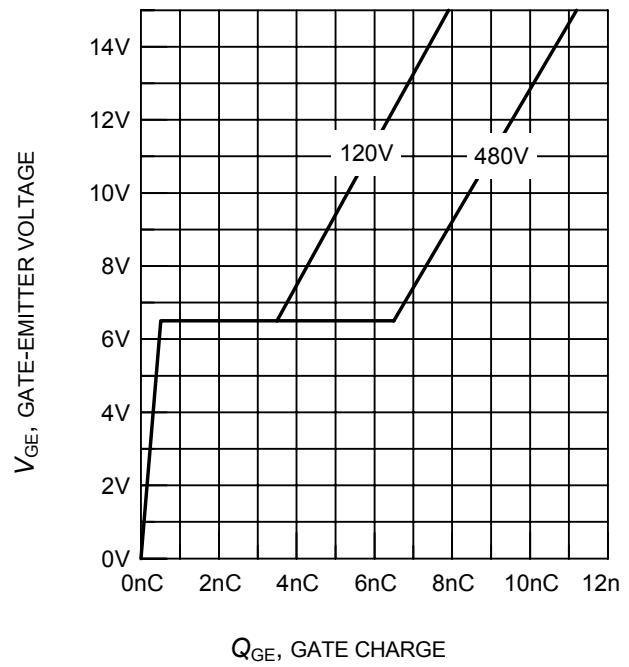


Figure 17. Typical gate charge
($I_C = 3\text{A}$)

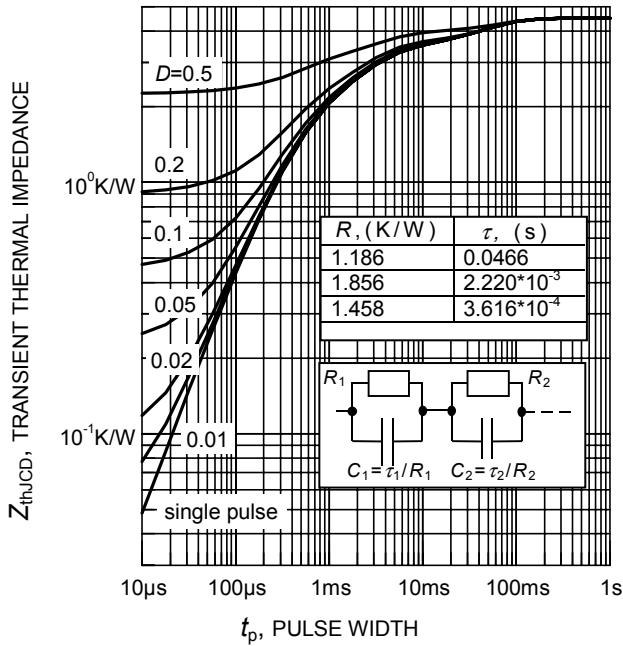


Figure 18. IGBT transient thermal impedance as a function of pulse width ($D = t_p / T$)

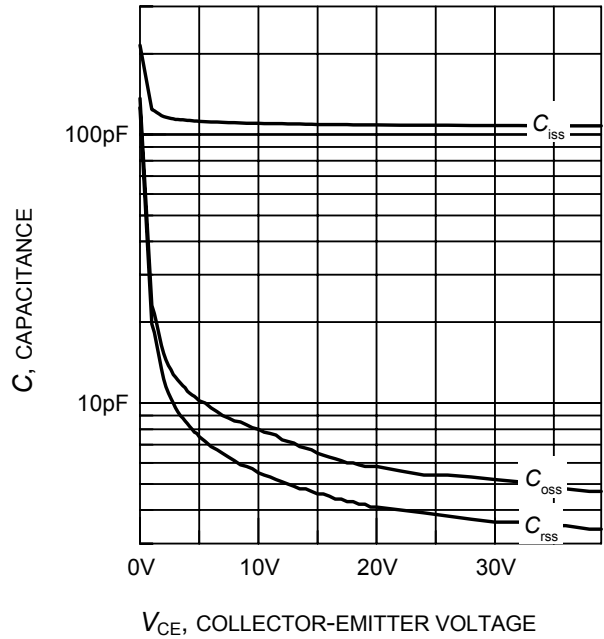


Figure 19. Typical capacitance as a function of collector-emitter voltage ($V_{GE} = 0V, f = 1MHz$)

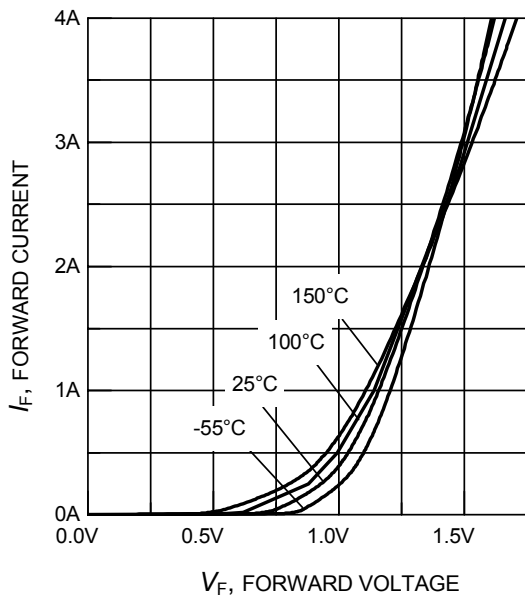


Figure 20. Typical diode forward current as a function of forward voltage

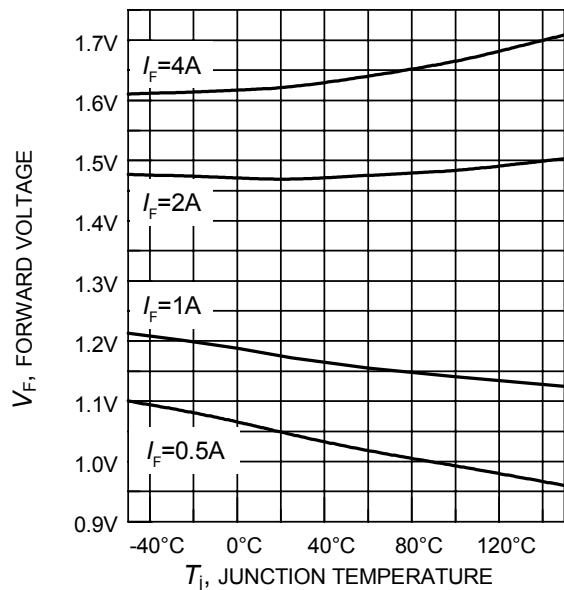
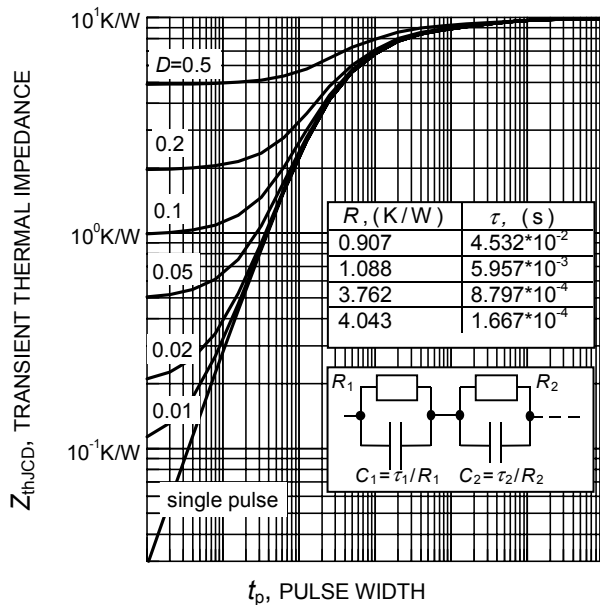


Figure 21. Typical diode forward voltage as a function of junction temperature



t_p , PULSE WIDTH
Figure 22. Diode transient thermal impedance as a function of pulse width
 $(D = t_p / T)$

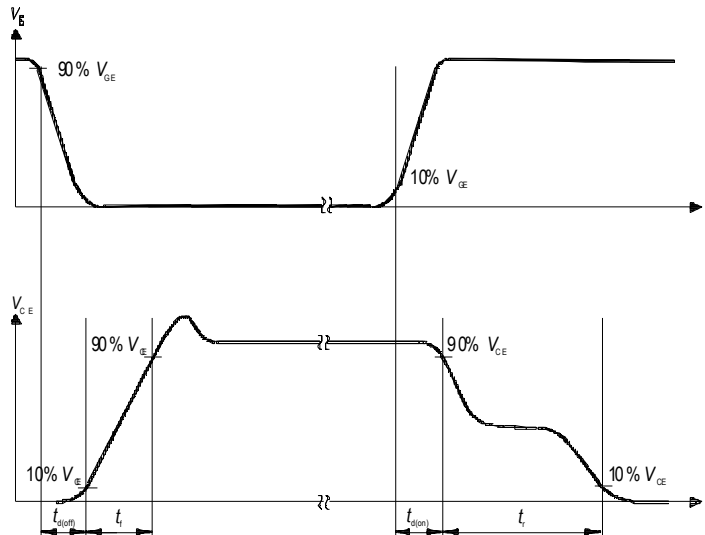


Figure A. Definition of switching times

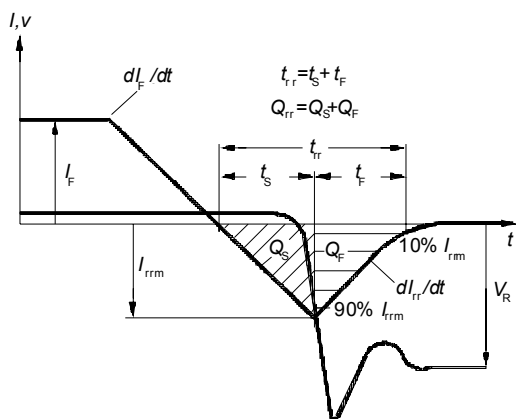


Figure B. Definition of diodes switching characteristics

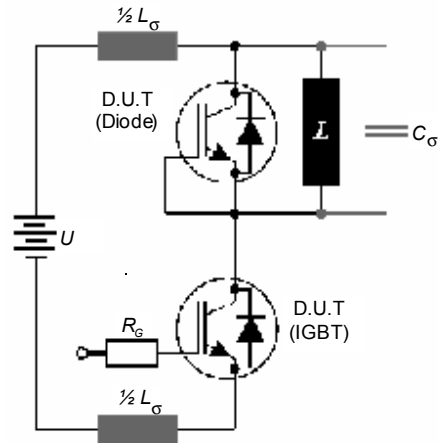
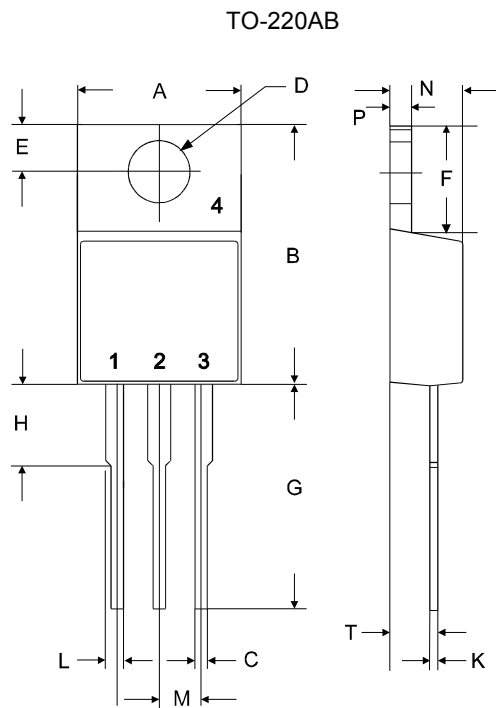
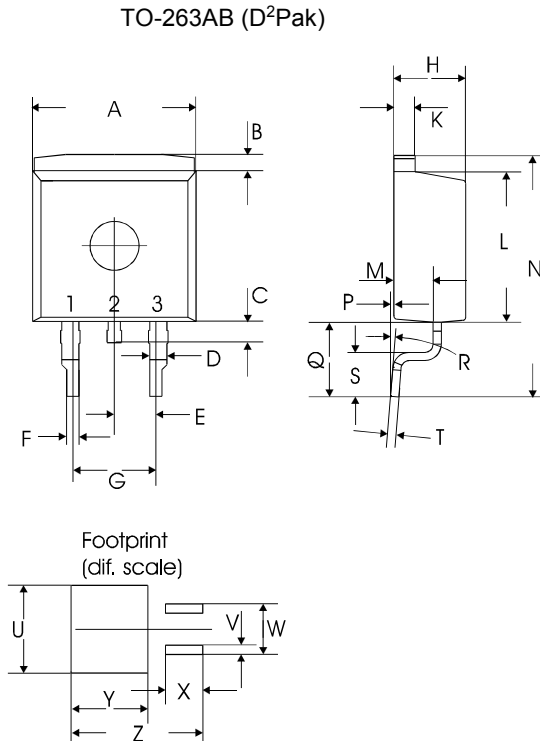


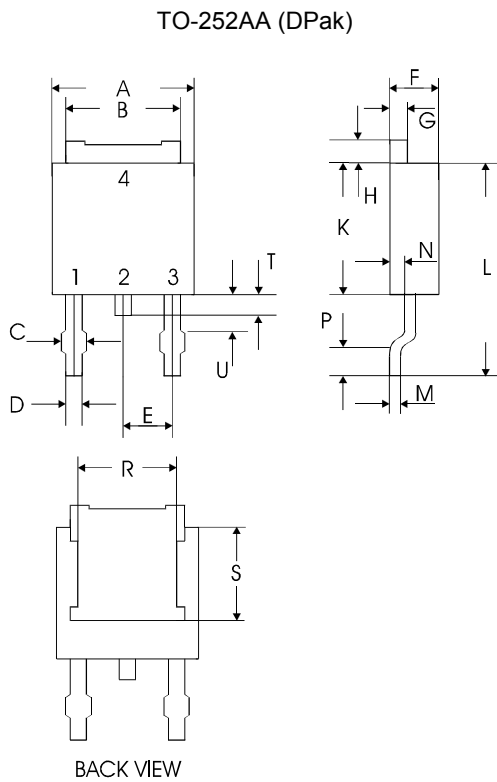
Figure C. Dynamic test circuit



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.80	10.20	0.3858	0.4016
B	0.70	1.30	0.0276	0.0512
C	1.00	1.60	0.0394	0.0630
D	1.03	1.07	0.0406	0.0421
E	2.54 typ.		0.1 typ.	
F	0.65	0.85	0.0256	0.0335
G	5.08 typ.		0.2 typ.	
H	4.30	4.50	0.1693	0.1772
K	1.17	1.37	0.0461	0.0539
L	9.05	9.45	0.3563	0.3720
M	2.30	2.50	0.0906	0.0984
N	15 typ.		0.5906 typ.	
P	0.00	0.20	0.0000	0.0079
Q	4.20	5.20	0.1654	0.2047
R	8° max		8° max	
S	2.40	3.00	0.0945	0.1181
T	0.40	0.60	0.0157	0.0236
U	10.80		0.4252	
V	1.15		0.0453	
W	6.23		0.2453	
X	4.60		0.1811	
Y	9.40		0.3701	
Z	16.15		0.6358	



symbol	dimensions			
	[mm]		symbol	
	min		min	
A	6.40	A	6.40	A
B	5.25	B	5.25	B
C	(0.65)	C	(0.65)	C
D	0.63	D	0.63	D
E	2.28		E	
F	2.19	F	2.19	F
G	0.76	G	0.76	G
H	0.90	H	0.90	H
K	5.97	K	5.97	K
L	9.40	L	9.40	L
M	0.46	M	0.46	M
N	0.87	N	0.87	N
P	0.51	P	0.51	P
R	5.00	R	5.00	R
S	4.17	S	4.17	S
T	0.26	T	0.26	T
U	-	U	-	U



ILP03N60, ILB03N60 ILD03N60

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